ABSTRACT

This invention relates to a method of fabrication used for semiconductor integrated circuit devices, and more specifically to the use an alternate etch stop in dual damascene interconnects that improves adhesion between low dielectric constant organic materials. In addition, the etch stop material is a silicon containing material and is transformed into a low dielectric constant material (k = 3.5 to 5), which becomes silicon-rich silicon oxide after UV radiation and silylation, oxygen plasma.

FIGURE 6